

# PS9331L, PS9331L2

R08DS0111EJ0200 Rev.2.00 Jun 21, 2013

2.5 A OUTPUT CURRENT, HIGH CMR, IGBT GATE DRIVE, 6-PIN SDIP PHOTOCOUPLER

#### **DESCRIPTION**

The PS9331L and PS9331L2 are optical coupled isolators containing a GaAlAs LED on the input side and a photo diode, a signal processing circuit and power MOSFETs on the output side on one chip.

The PS9331L and PS9331L2 are in 6-pin plastic SDIP (Shrink Dual In-line Package). The PS9331L2 has 8 mm creepage distance. The mount area of 6-pin plastic SDIP is half size of 8-pin DIP.

The PS9331L and PS9331L2 are designed specifically for high common mode transient immunity (CMR) and high switching speed. It is suitable for driving IGBTs and MOS FETs.

The PS9331L is lead bending type (Gull-wing) for surface mounting.

The PS9331L2 is lead bending type for long creepage distance (Gull-wing) for surface mount.

#### **FEATURES**

- Long creepage distance (8 mm MIN.: PS9331L2)
- Half size of 8-pin DIP
- Peak output current (2.5 A MAX., 2.0 A MIN.)
- High speed switching ( $t_{PLH}$ ,  $t_{PHL} = 175$  ns MAX.)
- High common mode transient immunity (CM<sub>H</sub>, CM<sub>L</sub> =  $\pm 50 \text{ kV/}\mu\text{s}$  MIN.)
- Operating Ambient Temperature (125 °C)
- Embossed tape product: PS9331L-E3, PS9331L2-E3: 2 000 pcs/reel
- Pb-Free product
- · Safety standards
  - UL approved: No. E72422
  - CSA approved: No. CA 101391 (CA5A, CAN/CSA-C22.2 60065, 60950)
  - SEMKO approved (EN 60065, EN 60950)
  - DIN EN 60747-5-5 (VDE 0884-5) approved (Option)

# PIN CONNECTION (Top View) 6 5 4 1. Anode 2. NC 3. Cathode 4. Vee 5. Vo 6. Vcc

#### **APPLICATIONS**

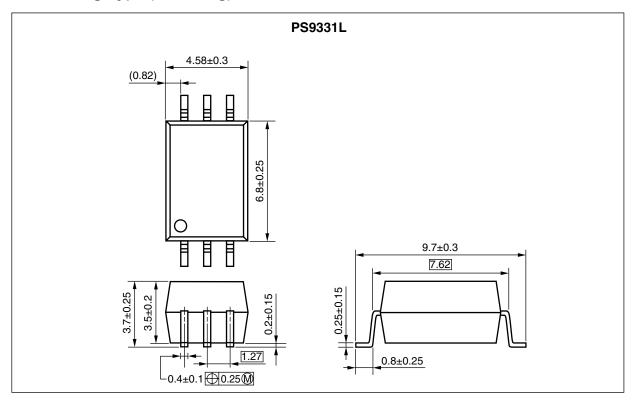
- IGBT, Power MOS FET Gate Driver
- Industrial inverter
- AC Servo

The mark <R> shows major revised points.

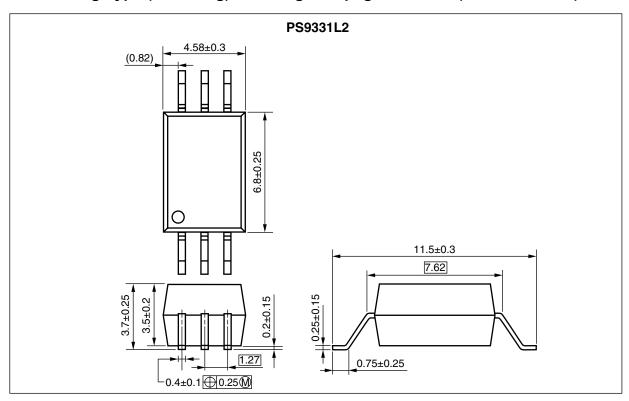
The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

#### PACKAGE DIMENSIONS (UNIT: mm)

#### Lead Bending Type (Gull-wing) For Surface Mount



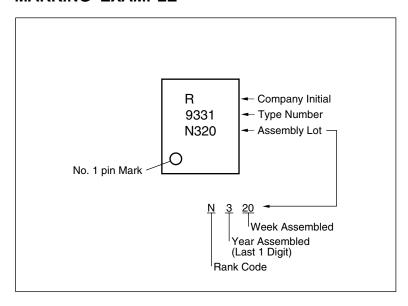
#### Lead Bending Type (Gull-wing) For Long Creepage Distance (Surface Mount)



#### PHOTOCOUPLER CONSTRUCTION

Parameter	PS9331L	PS9331L2	
Air Distance (MIN.)	7 mm	8 mm	
Outer Creepage Distance (MIN.)	7 mm	8 mm	
Isolation Distance (MIN.)	0.4 mm	0.4 mm	

#### **MARKING EXAMPLE**



#### **ORDERING INFORMATION**

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number*1
PS9331L	PS9331L-AX	Pb-Free	20 pcs (Tape 20 pcs cut)	Standard	PS9331L
PS9331L-E3	PS9331L-E3-AX	(Ni/Pd/Au)	Embossed Tape 2 000	products	
			pcs/reel	(UL, CSA,	
PS9331L2	PS9331L2-AX		20 pcs (Tape 20 pcs cut)	SEMKO	PS9331L2
PS9331L2-E3	PS9331L2-E3-AX		Embossed Tape 2 000	approved)	
			pcs/reel		
PS9331L-V	PS9331L-V-AX		20 pcs (Tape 20 pcs cut)	DIN EN 60747-5-5	PS9331L
PS9331L-V-E3	PS9331L-V-E3-AX		Embossed Tape 2 000	(VDE 0884-5)	
			pcs/reel	approved	
PS9331L2-V	PS9331L2-V-AX		20 pcs (Tape 20 pcs cut)	(Option)	PS9331L2
PS9331L2-V-E3	PS9331L2-V-E3-AX		Embossed Tape 2 000		
			pcs/reel		

Note: \*1. For the application of the Safety Standard, following part number should be used.

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

	Parameter	Symbol	Ratings	Unit
Diode	Forward Current	I <sub>F</sub>	25	mA
	Peak Transient Forward Current (Pulse Width < 1 μs)	I <sub>F (TRAN)</sub>	1.0	А
	Reverse Voltage	$V_R$	5	V
	Power Dissipation *1	P <sub>D</sub>	45	mW
Detector	High Level Peak Output Current *2	I <sub>OH (PEAK)</sub>	2.5	Α
	Low Level Peak Output Current *2	I <sub>OL (PEAK)</sub>	2.5	Α
	Supply Voltage	(V <sub>CC</sub> – V <sub>EE</sub> )	0 to 35	V
	Output Voltage	Vo	0 to V <sub>CC</sub>	V
Power Dissipation *3		Pc	250	mW
Isolation Voltage *4		BV	5 000	Vr.m.s.
Operating Frequency		f	50	kHz
Operating Ambient Temperature		T <sub>A</sub>	-40 to +125	°C
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C

Notes: \*1. Reduced to 1.2 mW/ $^{\circ}$ C at T<sub>A</sub> = 110 $^{\circ}$ C or more.

#### RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	$(V_{CC} - V_{EE})$	15		30	V
Forward Current (ON)	I <sub>F (ON)</sub>	8	10	12	mA
Forward Voltage (OFF)	V <sub>F (OFF)</sub>	-2		0.8	V
Operating Ambient Temperature	T <sub>A</sub>	-40		125	°C

<sup>\*2.</sup> Maximum pulse width = 10  $\mu$ s, Maximum duty cycle = 0.2%

<sup>\*3.</sup> Reduced to 3.9 mW/°C at  $T_A$  = 85°C or more.

<sup>\*4.</sup> AC voltage for 1 minute at  $T_A$  = 25°C, RH = 60% between input and output. Pins 1-3 shorted together, 4-6 shorted together.

# ELECTRICAL CHARACTERISTICS (at RECOMMENDED OPERATING CONDITIONS, $V_{\text{EE}}$ = GND, unless otherwise specified)

Parameter		Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Diode	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	1.35	1.56	1.75	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 3 V, T <sub>A</sub> = 25°C			10	μΑ
	Input Capacitance	C <sub>IN</sub>	$f = 1 \text{ MHz}, V_F = 0 \text{ V}$		30		pF
Detector	High Level Output Current	I <sub>OH</sub>	$V_{\rm O} = (V_{\rm CC} - 4 \text{ V})^{*2}$	0.5	2.2		Α
			$V_{\rm O} = (V_{\rm CC} - 15 \text{ V})^{*3}$	2.0			
	Low Level Output Current	I <sub>OL</sub>	$V_{O} = (V_{EE} + 2.5 \text{ V})^{*2}$	0.5	2.4		Α
			$V_{O} = (V_{EE} + 15 \text{ V})^{*3}$	2.0			
	High Level Output Voltage		$I_{\rm O}$ = -100 mA *4	V <sub>CC</sub> - 3.0	V <sub>CC</sub> – 1.3		V
	Low Level Output Voltage		I <sub>O</sub> = 100 mA		0.2	0.5	V
	High Level Supply Current		V <sub>O</sub> = Open		1.7	2.2	mA
	Low Level Supply Current	I <sub>CCL</sub>	V <sub>O</sub> = Open		1.7	2.2	mA
	UVLO Threshold	$V_{UVLO^+}$	$V_O > 5 V$ , $I_F = 10 mA$	10.8	12.3	13.4	V
		V <sub>UVLO</sub> -		9.5	11.0	12.5	
	UVLO Hysteresis	UVLO <sub>HYS</sub>	$V_O > 5 V$ , $I_F = 10 mA$	0.4	1.3		V
Coupled	Threshold Input Current	I <sub>FLH</sub>	$I_{O} = 0 \text{ mA}, V_{O} > 5 \text{ V}$		1.7	4.0	mA
		V <sub>FHL</sub>	I <sub>O</sub> = 0 mA, V <sub>O</sub> < 5 V	0.8			V

Notes: \*1. Typical values at  $T_A = 25^{\circ}C$ ,  $V_{CC} - V_{EE} = 30 \text{ V}$ .

# SWITCHING CHARACTERISTICS (at RECOMMENDED OPERATING CONDITIONS, $V_{EE} = GND$ , unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Propagation Delay Time (L $\rightarrow$ H)	t <sub>PLH</sub>	$R_g = 10 \Omega, C_g = 10 nF,$		80	175	ns
Propagation Delay Time (H $\rightarrow$ L)	t <sub>PHL</sub>	f = 10 kHz,		105	175	ns
Pulse Width Distortion (PWD)	t <sub>PHL</sub> -t <sub>PLH</sub>	Duty Cycle = 50%,		25	75	ns
Propagation Delay Time	t <sub>PHL</sub> —t <sub>PLH</sub>	I <sub>F</sub> = 10 mA	-90		90	ns
(Difference Between Any Two						
Products)						
Rise Time	$t_r$			40		ns
Fall Time	t <sub>f</sub>			40		ns
Common Mode Transient	CM <sub>H</sub>	$T_A = 25^{\circ}C$ , $I_F = 10$ mA,	50			kV/μs
Immunity at High Level Output		$V_{CC} = 30 \text{ V}, V_{CM} = 1.5 \text{ kV}$				
Common Mode Transient	CM <sub>L</sub>	$T_A = 25^{\circ}C, I_F = 0 \text{ mA},$	50			kV/ <i>μ</i> s
Immunity at Low Level Output		$V_{CC} = 30 \text{ V}, V_{CM} = 1.5 \text{ kV}$				

Notes: \*1. Typical values at  $T_A = 25$ °C,  $V_{CC}$ – $V_{EE} = 30$  V.

<sup>\*2.</sup> Maximum pulse width = 50  $\mu$ s, Maximum duty cycle = 0.5%.

<sup>\*3.</sup> Maximum pulse width = 10  $\mu$ s, Maximum duty cycle = 0.2%.

<sup>\*4.</sup> V<sub>OH</sub> is measured with the DC load current in this testing (Maximum pulse width = 2 ms, Maximum duty cycle = 20%).

#### **TEST CIRCUIT**

Fig. 1 Іон Test Circuit Fig. 2 lo∟ Test Circuit  $V_{\text{CC}}$ Vcc \_1.0 μF Fig. 3 Von Test Circuit Fig. 4 Vol Test Circuit  $V_{\text{CC}}$  $V_{\text{CC}}$ 1.0 μF L 1.0μF Vон VOL 100 mA 100 mA Fig. 6 UVLO Test Circuit Fig. 5 Icch/IccL Test Circuit  $V_{\text{CC}}$ I<sub>F</sub> = 10 mA <sup>‡</sup> 1.0*μ*F <sup>⊥</sup> 1.0*μ*F --Vo>5 V



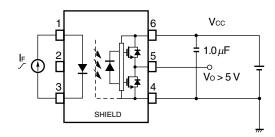
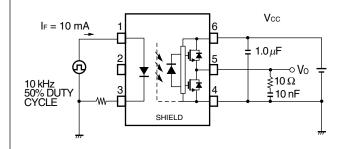


Fig. 8 tplh, tphl, tr, tf Test Circuit and Wave Forms



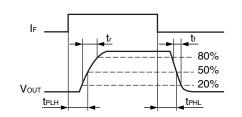
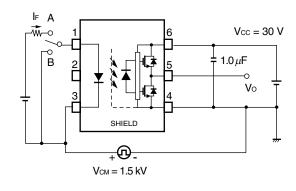
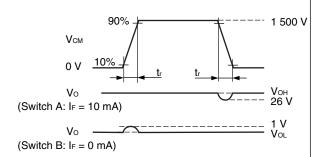
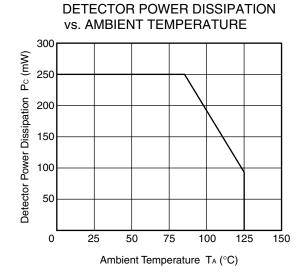


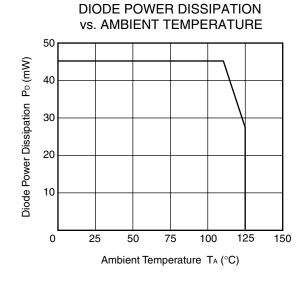
Fig. 9 CMR Test Circuit and Wave Forms

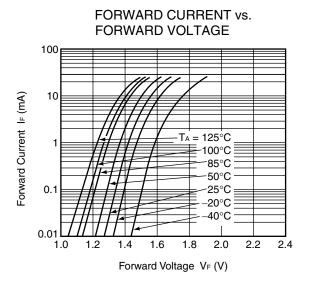


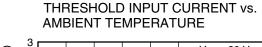


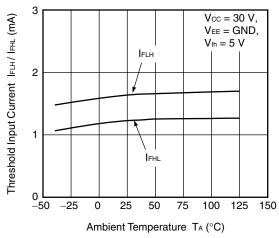
#### <R> TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)

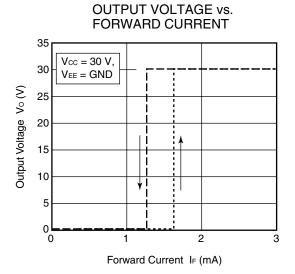




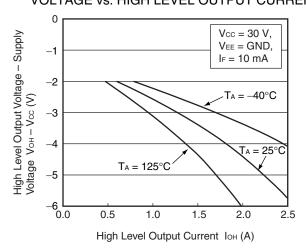






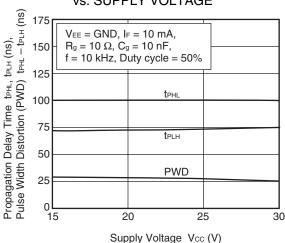


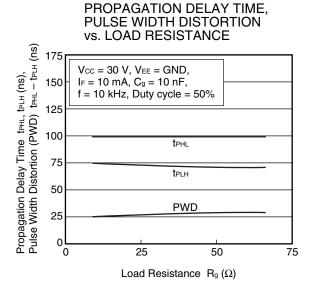
HIGH LEVEL OUTPUT VOLTAGE – SUPPLY VOLTAGE vs. HIGH LEVEL OUTPUT CURRENT



**Remark** The graphs indicate nominal characteristics.

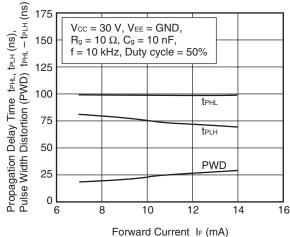
#### LOW LEVEL OUTPUT VOLTAGE vs. LOW LEVEL OUTPUT CURRENT 6 Low Level Output Voltage Vo∟(V) Vcc = 30 VVEE = GND. $T_A = 125^{\circ}C$ $I_F = 0 \text{ mA}$ 4 $T_A = 25^{\circ}C$ 2 0.0 0.5 1.0 1.5 2.0 25 Low Level Output Current IoL (A) PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. SUPPLY VOLTAGE



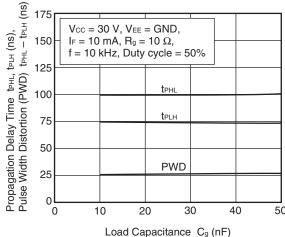


Remark The graphs indicate nominal characteristics.

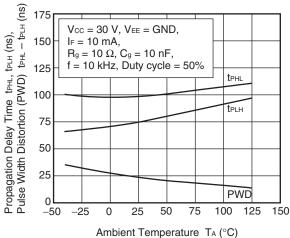
#### PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. FORWARD CURRENT

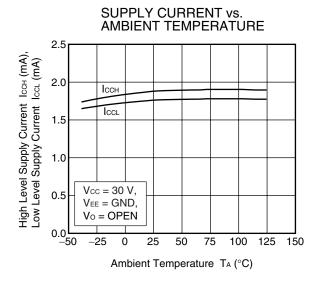


#### PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD CAPACITANCE

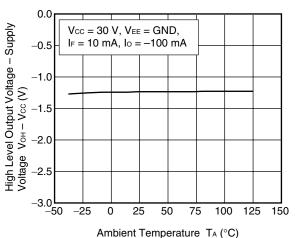


# PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

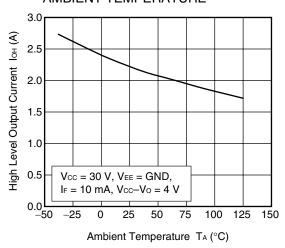




# HIGH LEVEL OUTPUT VOLTAGE – SUPPLY VOLTAGE vs. AMBIENT TEMPERATURE

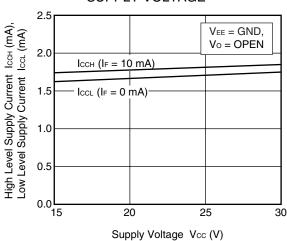


# HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

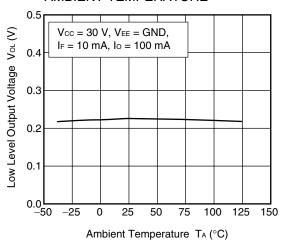


**Remark** The graphs indicate nominal characteristics.

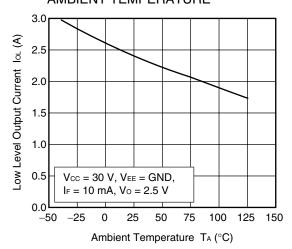
# SUPPLY CURRENT vs. SUPPLY VOLTAGE



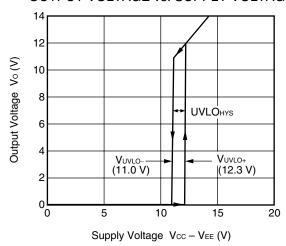
# LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



# LOW LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

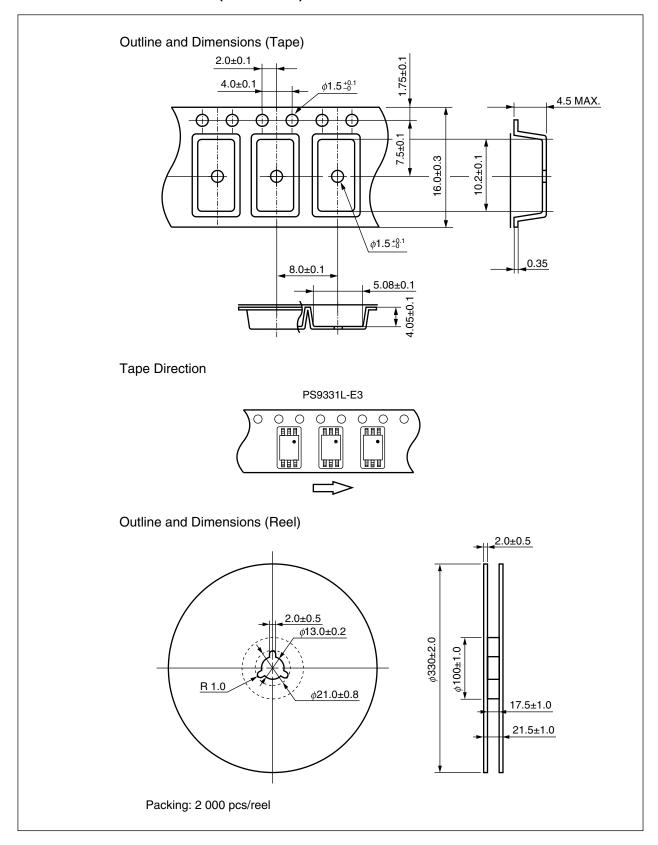


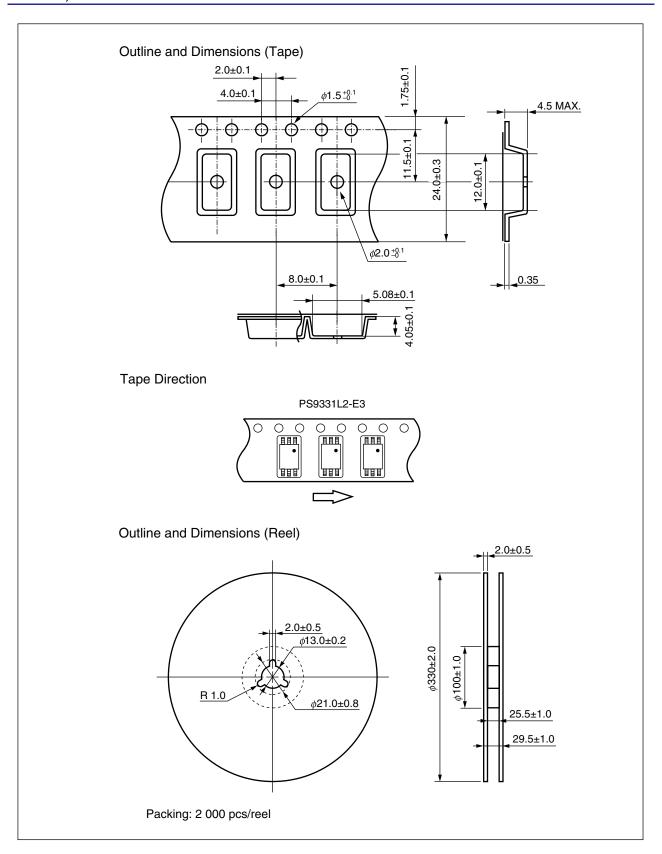
#### OUTPUT VOLTAGE vs. SUPPLY VOLTAGE



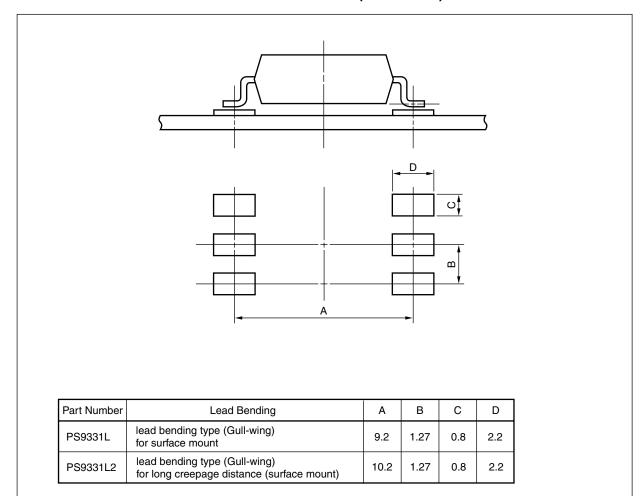
**Remark** The graphs indicate nominal characteristics.

#### TAPING SPECIFICATIONS (UNIT: mm)





## RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



#### NOTES ON HANDLING

- 1. Recommended soldering conditions
  - (1) Infrared reflow soldering
    - Peak reflow temperature 260°C or below (package surface temperature)
    - Time of peak reflow temperature
    - Time of temperature higher than 220°C
    - Time to preheat temperature from 120 to 180°C
    - Number of reflows
    - Flux

10 seconds or less

60 seconds or less

 $120 \pm 30 \text{ s}$ 

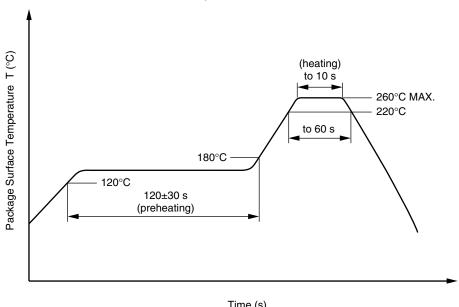
Three

Rosin flux containing small amount of chlorine (The flux

with a maximum chlorine content of 0.2 Wt% is

recommended.)

#### Recommended Temperature Profile of Infrared Reflow



Time (s)

#### (2) Wave soldering

Temperature 260°C or below (molten solder temperature)

Time 10 seconds or less

Preheating conditions 120°C or below (package surface temperature)

Number of times One (Allowed to be dipped in solder including plastic mold portion.)

Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine

content of 0.2 Wt% is recommended.)

#### (3) Soldering by Soldering Iron

Peak Temperature (lead part temperature) 350°C or below

Time (each pins) 3 seconds or less

Flux Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt% is recommended.)

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead

#### (4) Cautions

 Fluxes Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

#### 2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

#### **USAGE CAUTIONS**

- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. Board designing
  - (1) By-pass capacitor of more than 1.0  $\mu$ F is used between  $V_{CC}$  and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
  - (2) When designing the printed wiring board, ensure that the pattern of the IGBT collectors/emitters is not too close to the input block pattern of the photocoupler. If the pattern is too close to the input block and coupling occurs, a sudden fluctuation in the voltage on the IGBT output side might affect the photocoupler's LED input, leading to malfunction or degradation of characteristics. (If the pattern needs to be close to the input block, to prevent the LED from lighting during the off state due to the abovementioned coupling, design the input-side circuit so that the bias of the LED is reversed, within the
  - (3) Pin 2 (which is an NC\*1 pin) can either be connected directly to the GND pin on the LED side or left open. Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.

range of the recommended operating conditions, and be sure to thoroughly evaluate operation.)

- Note: \*1. NC: Non-Connection (No Connection).
- 3. Make sure the rise/fall time of the forward current is 0.5  $\mu$ s or less.
- 4. In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is  $3 \text{ V}/\mu \text{s}$  or less.
- 5. Avoid storage at a high temperature and high humidity.

#### SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/125/21	
Dielectric strength			
maximum operating isolation voltage	$U_IORM$	1 130	$V_{peak}$
Test voltage (partial discharge test, procedure a for type test and random test)	$U_pr$	1 808	$V_{peak}$
$U_{pr} = 1.6 \times U_{IORM.}$ , $P_d < 5 pC$			
Test voltage (partial discharge test, procedure b for all devices)	$U_pr$	2 119	$V_{peak}$
$U_{pr} = 1.875 \times U_{IORM.}, P_d < 5 pC$			
Highest permissible overvoltage	$U_TR$	8 000	$V_{peak}$
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	CTI	175	
Material group (DIN EN 60664-1 VDE0110 Part 1)		III a	
Storage temperature range	$T_{stg}$	-55 to +150	°C
Operating temperature range	$T_A$	-40 to +125	°C
Isolation resistance, minimum value			
$V_{IO}$ = 500 V dc at $T_A$ = 25°C	Ris MIN.	10 <sup>12</sup>	Ω
V <sub>IO</sub> = 500 V dc at T <sub>A</sub> MAX. at least 100°C	Ris MIN.	10 <sup>11</sup>	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal			
derating curve)			
Package temperature	Tsi	175	°C
Current (input current I <sub>F</sub> , Psi = 0)	Isi	400	mA
Power (output or total power dissipation)	Psi	700	mW
Isolation resistance			
$V_{IO}$ = 500 V dc at $T_A$ = Tsi	Ris MIN.	10 <sup>9</sup>	Ω

#### Caution

**GaAs Products** 

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
  - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

**Revision History** 

#### PS9331L, PS9331L2 Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	May 24, 2013	_	First edition issued	
2.00	Jun 21, 2013	pp.8 to 11	Addition of TYPICAL CHARACTERISTICS	

#### Notice

- 1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information,
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